

### **isc Silicon NPN Power Transistor**

# 2SD1727

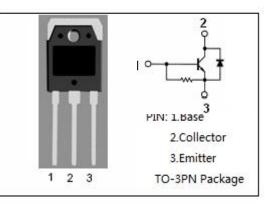
#### DESCRIPTION

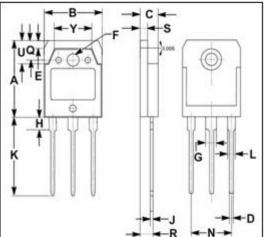
- High Voltage
- · High Switching Speed
- Built-in damper diode
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

• Designed for horizontal deflection output applications.

#### ABSOLUTE MAXIMUM RATINGS (Ta=25℃) SYMBOL PARAMETER VALUE UNIT Collector-Base Voltage 1500 V<sub>СВО</sub> V VCES Collector-Emitter Voltage 1500 V VCEO Collector-Emitter Voltage 700 V $V_{\text{EBO}}$ Emitter-Base Voltage 7 V **Collector Current-Continuous** $I_{C}$ 1.5 А Collector Current-Peak 5 А **I**CP Base Current- Continuous 0.6 А lΒ Collector Power Dissipation 60 W Pc @Tc=25°C Ti Junction Temperature 150 °C -55-150 Storage Temperature Range °C Tstg





	mm	
DIM	MIN	MAX
Α	19.60	20.30
В	15.50	15.70
С	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
Н	3.20	3.40
J	0.595	0.605
Κ	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

isc website: <u>www.iscsemi.com</u>



## **isc Silicon NPN Power Transistor**

# 2SD1727

### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 200mA; I <sub>C</sub> = 0	7			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.4A			8.0	V
$V_{BE(\text{sat})}$	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1Α; I <sub>B</sub> = 0.4Α			1.5	V
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V	5		25	
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 750V; I <sub>E</sub> = 0			10	μA
		V <sub>CB</sub> = 1500V; I <sub>E</sub> = 0			1.0	mA
$V_{\text{ECF}}$	C-E Diode Forward Voltage	I <sub>F</sub> = 1.5A			1.5	V
f⊤	Transition Frequency	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		2		MHz

Switching Times, Resistive Load

ts	Storage Time	I_c= 1A; I_{B1}= 0.3A; I_{B2}= 0.6A, V_{CC}= 200V	1.0	μs
t <sub>f</sub>	Fall Time		0.2	μ <b>S</b>

### **NOTICE:**

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.